

ABSTRACT

A method and apparatus are provided for reducing leakage current in a read only memory device. Leakage current is reduced by reducing the duration of the precharge cycle during each read cycle so that the associated leakage current will flow for a shorter time period during each cycle. The precharge phase is positioned at the beginning of each read cycle, prior to the evaluation phase. The precharge phase is terminated by a subsequent clock edge or by an internal time out prior to a subsequent clock edge. The time interval between when the columns reach their precharge voltage and the evaluation phase begins is reduced.

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